

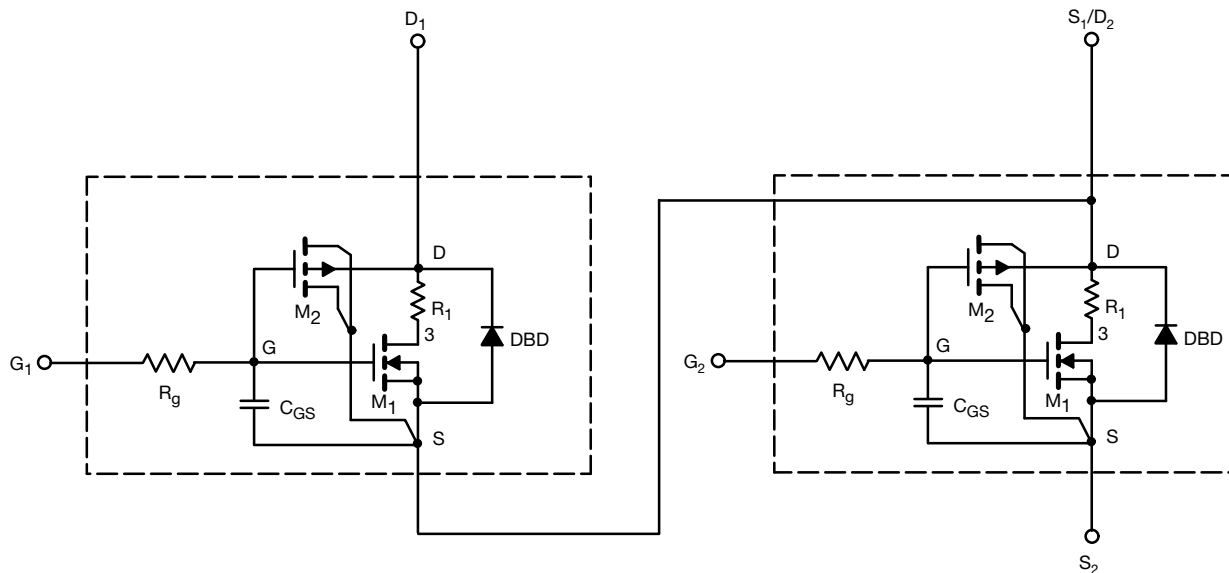
## Dual N-Channel 30 V (D-S) MOSFET

### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### SUBCIRCUIT MODEL SCHEMATIC



### CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT	
<b>Static</b>						
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	Ch-1	1.6	-	V
			Ch-2	1.5	-	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9.8 A	Ch-1	0.020	0.020	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	Ch-2	0.009	0.009	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8.5 A	Ch-1	0.0265	0.0265	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12 A	Ch-2	0.0150	0.0135	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 9.8 A	Ch-1	26	30	S
		V <sub>DS</sub> = 10 V, I <sub>D</sub> = 15 A	Ch-2	25	30	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 8 A, V <sub>GS</sub> = 0 V	Ch-1	0.84	0.84	V
		I <sub>S</sub> = 10 A, V <sub>GS</sub> = 0 V	Ch-2	0.82	0.82	
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	Channel-1 V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz Channel-2 V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	Ch-1	397	400	pF
			Ch-2	716	730	
Output Capacitance	C <sub>oss</sub>		Ch-1	127	125	
			Ch-2	157	155	
Reverse Transfer Capacitance	C <sub>rss</sub>		Ch-1	24	25	
			Ch-2	66	65	
Total Gate Charge	Q <sub>g</sub>	Channel-1 V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9.8 A	Ch-1	6.2	7.4	nC
		Channel-2 V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	Ch-2	12	14.2	
		Channel-1 V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9.8 A	Ch-1	3	3.5	
			Ch-2	6	6.8	
Gate-Source Charge	Q <sub>gs</sub>	Channel-2 V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A	Ch-1	1.5	1.5	
			Ch-2	2.2	2.2	
Gate-Drain Charge	Q <sub>gd</sub>		Ch-1	1.1	1.1	
			Ch-2	2.3	2.3	

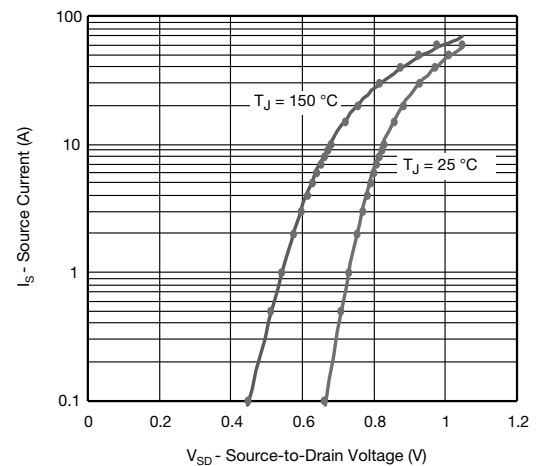
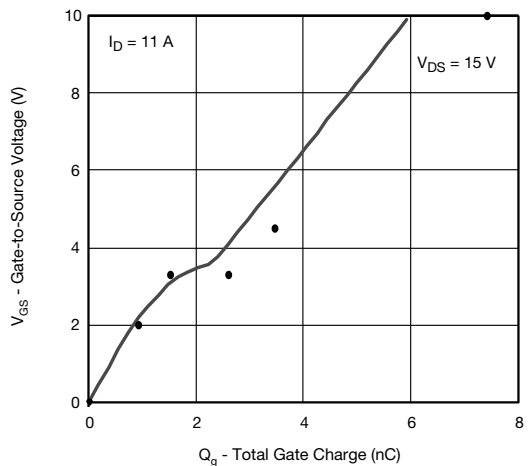
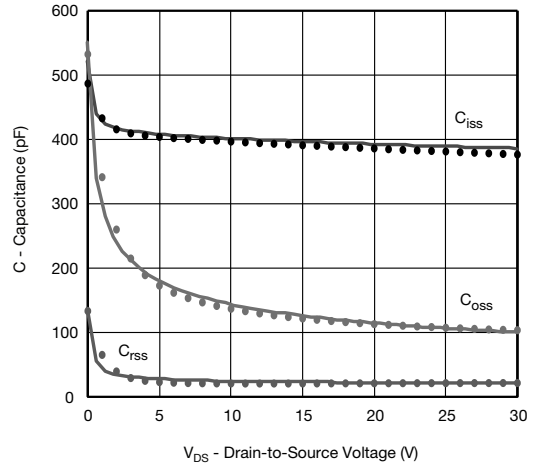
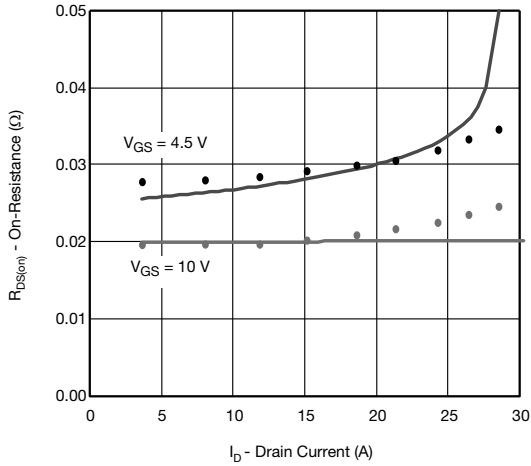
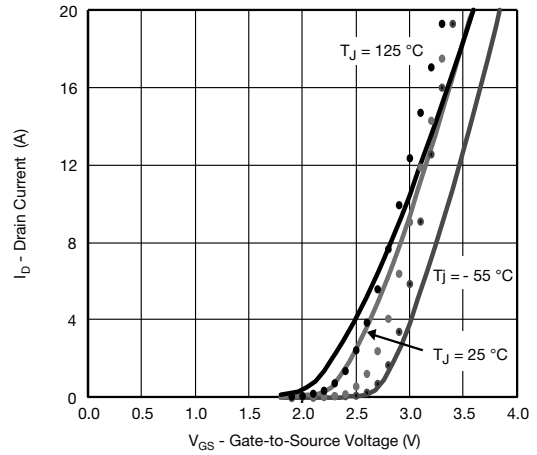
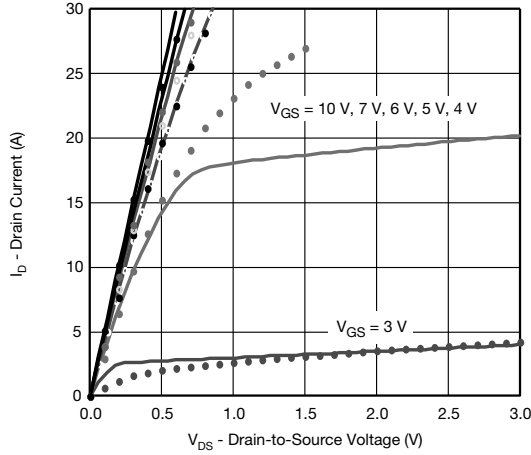
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.



## COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted

### Channel-1 MOSFET



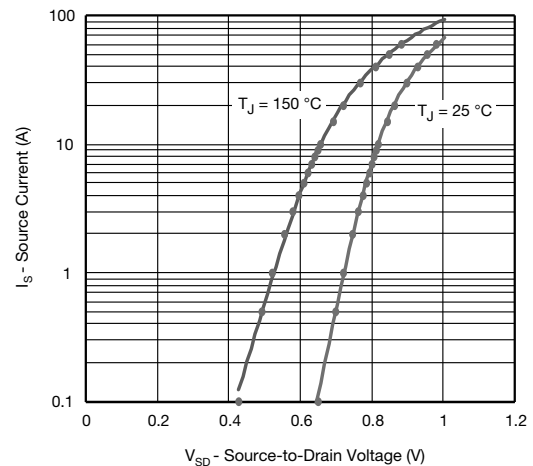
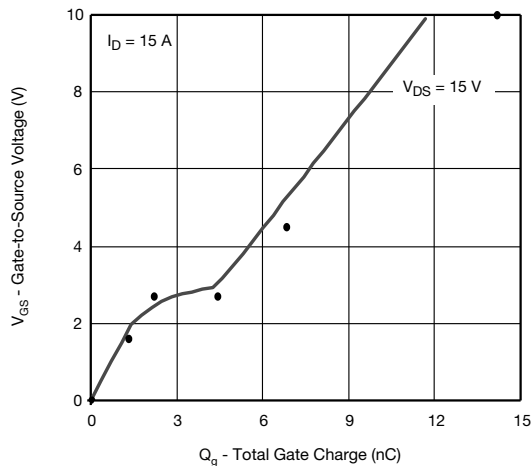
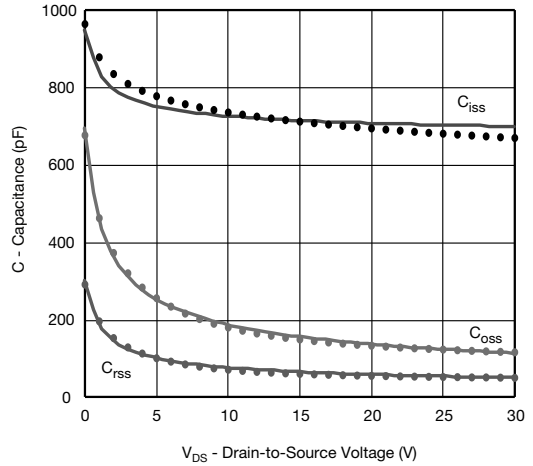
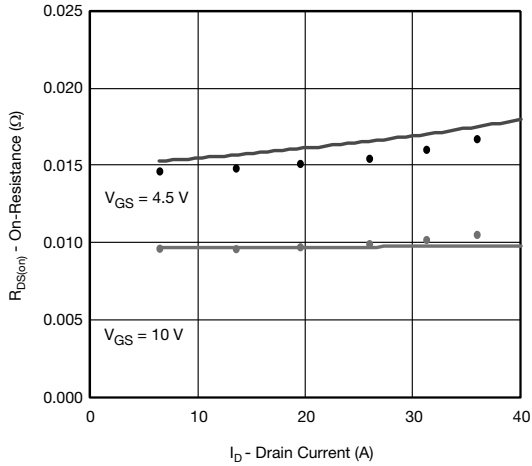
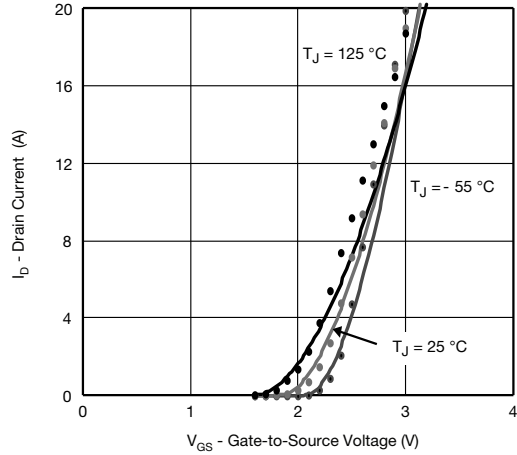
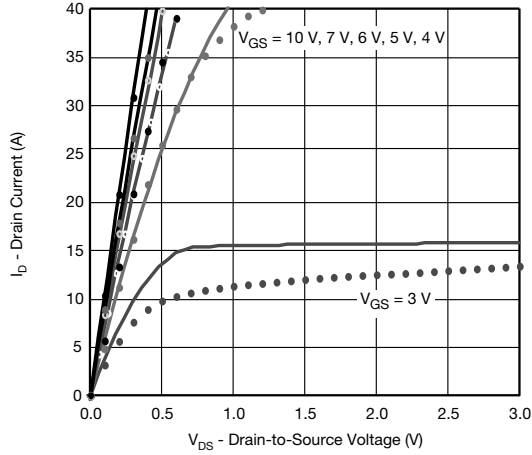
### Note

- Dots and squares represent measured data.



## COMPARISON OF MODEL WITH MEASURED DATA $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted

### Channel-2 MOSFET



#### Note

- Dots and squares represent measured data.



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